

OMERE

[COMET-ENV] Tools to predict Single Event Effects - 13 Dec 2022

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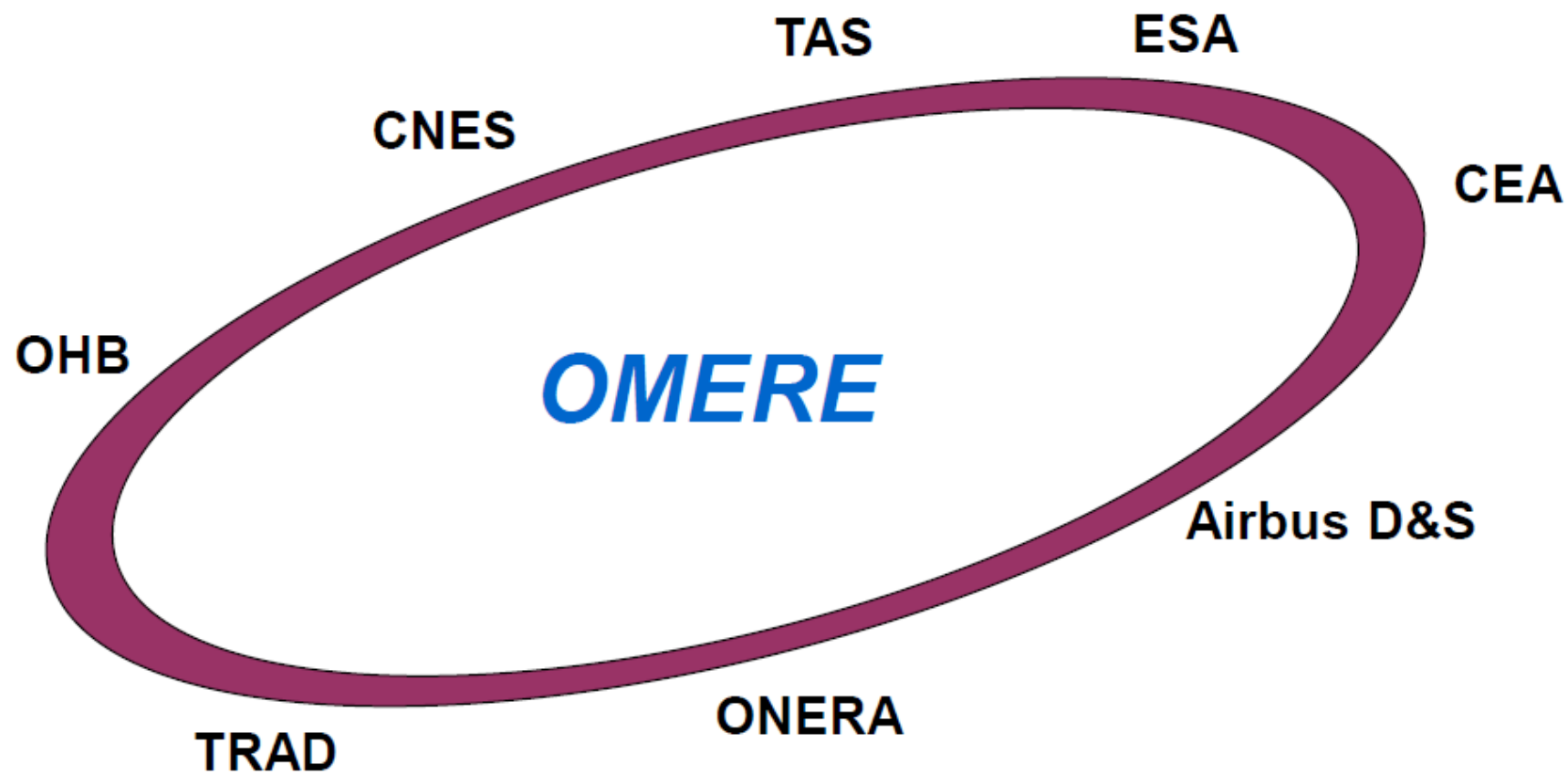
OMERE in summary

■ The project

- ❑ Since 1999
- ❑ TRAD development with CNES support
- ❑ Freeware for space radiation environment and effects on electronic components
- ❑ Stand alone software (no internet connection needed)
- ❑ Conceived to meet industrial requirements
- ❑ Integrates ONERA models
- ❑ Integrates outcomes of Research and Technology projects financed by CNES
- ❑ Coupling with FASTRAD.

OMERE in summary

- The partnership



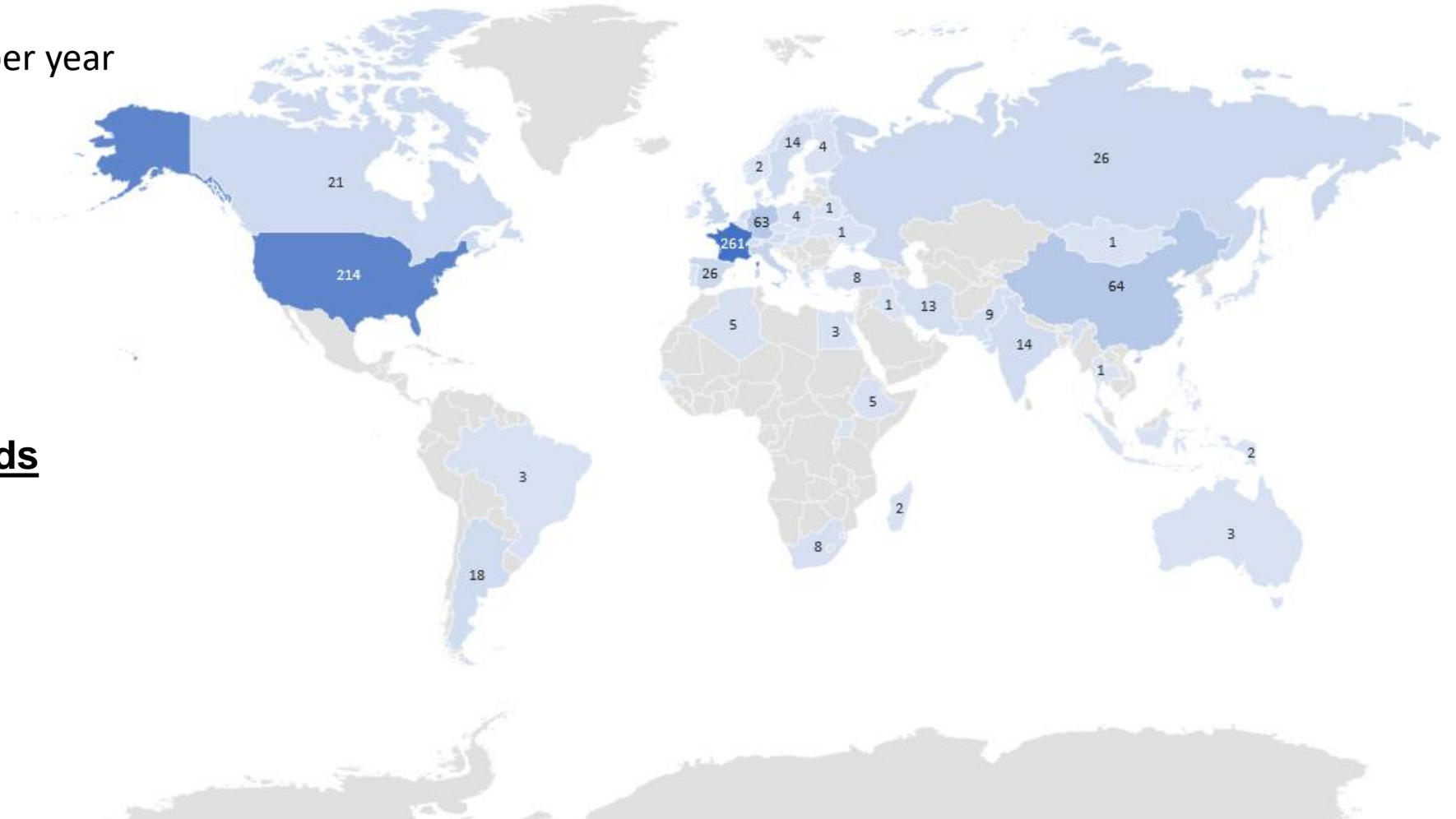
OMERE in summary

■ OMERE software

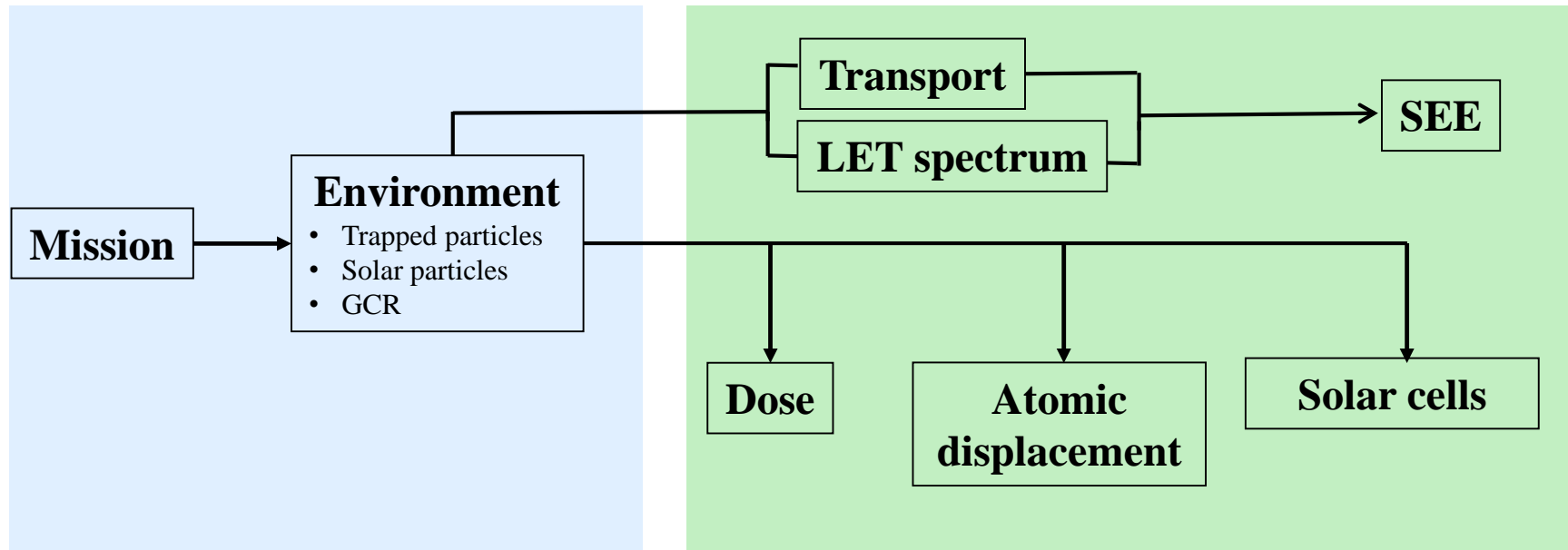
- ❑ One major release per year
- ❑ Support for users
- ❑ Radiation analysis
- ❑ Education purpose

Total number of downloads

2021
998



OMERE architecture



1- Defines the spectra around the spacecraft

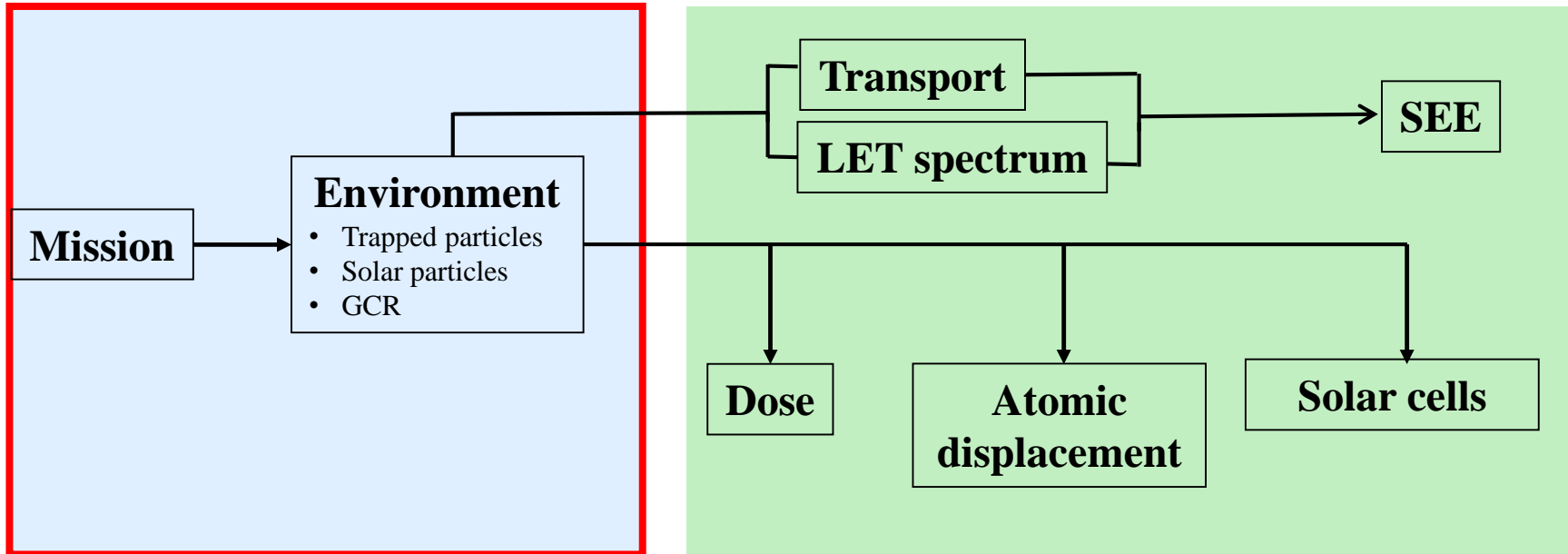
- Isotropic environment
- No shielding considered

2- Estimates the effects on components

- SEE rate, ionizing dose, non-ionizing dose
- Shielding: simple geometry



OMERE architecture



1- Defines the spectra around the spacecraft

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Environment engineering models

- Engineering models including (but not limited to) ECSS standards

- Models:

- In-situ measurements
- Range of validity of L and energy
- Standards

- Options:

- Solar min/max
- Confidence level [%]
- Magnetic field
- Magnetospheric cutoff

- Cosmic rays

- **GCR ISO 15390**
- CREME 86
- CREME 96

- Solar particles

- Protons (average)
 - **ESP**
 - JPL91
 - JPL91 Extended
 - SOLPRO
 - SPOF
 - SAPPHIRE
- Ions (average)
 - PSYCHIC
 - Helium
 - SAPPHIRE
- Solar flare models
 - CREME 86
 - **CREME 96**
 - IOFLAR
 - SAPPHIRE

- Trapped particles

- Electrons
 - **AE8**
 - **IGE 2006**
 - **MEO**
 - OZONE
 - SLOT
 - AE9
 - GREEN
- Protons
 - **AP8**
 - AP9
 - OPAL
 - GREEN

- *Magnetospheric cutoff*

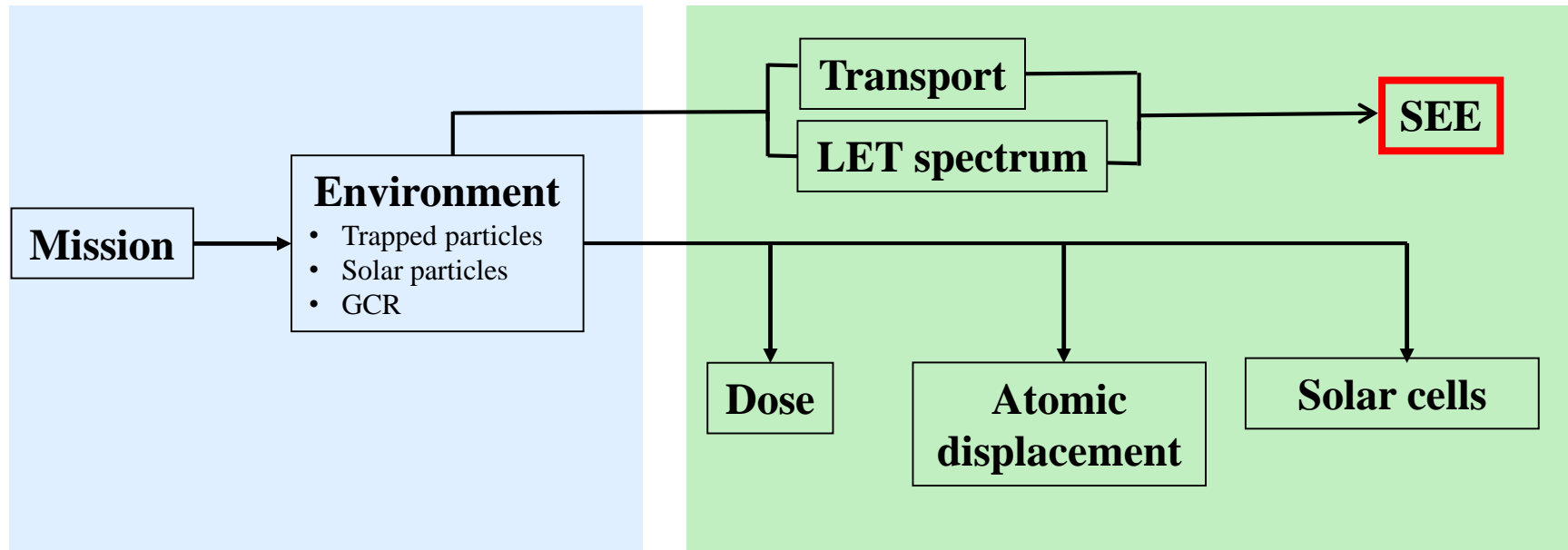
- **Störmer**
- ONERA

- *Magnetic field*

- **Jensen Cain**
- Dipolar
- IGRF
- GSFC



OMERE architecture



1- Defines the spectra around the spacecraft

- Isotropic environment
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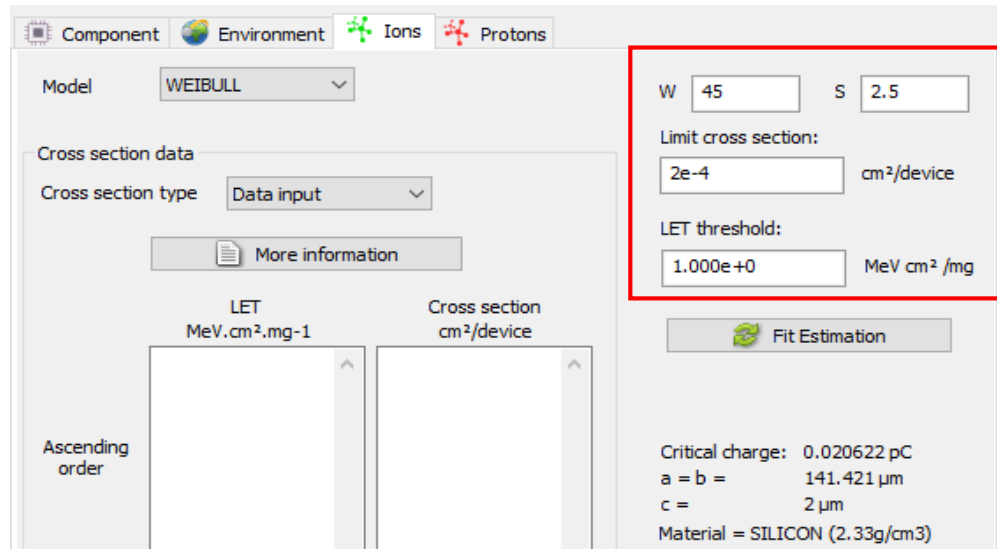
2- Estimates the effects on components

- SEE rate, ionizing dose, non-ionizing dose
- Shielding: simple geometry



Cross section

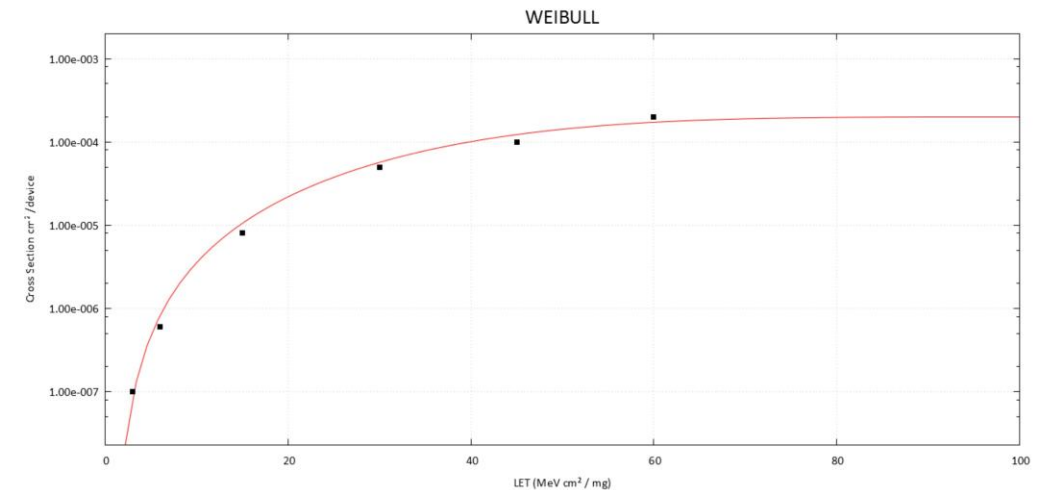
- SEE probability → device Cross Section



- Weibull curve
 - Weibull distribution (red curve) fitted to the test data (black dots)

- Weibull fit parameters
 - W (width)
 - S (shape)
 - σ_{SAT} (saturated cross section)
 - L_{th} (threshold LET)

$$F(L) = \sigma_0 \left[1 - \exp \left(- \left(\frac{L - L_0}{W} \right)^S \right) \right]$$



SEE caused by Ions: CREME and RPP Method

■ CREME (Cosmic Ray Effect on Electronics)

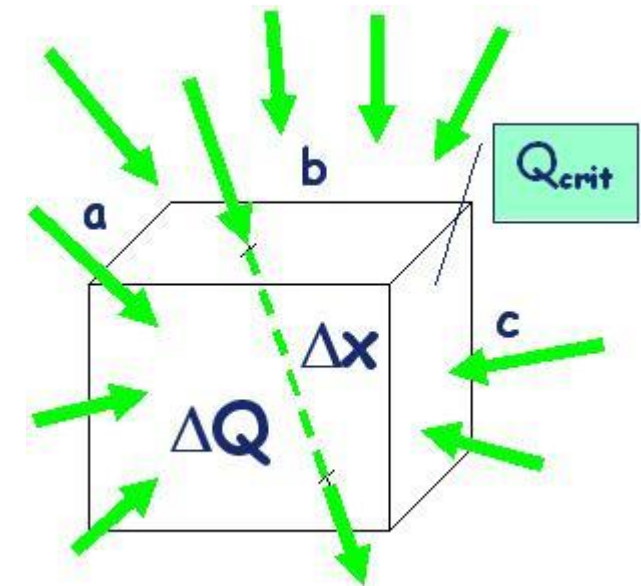
- Adams, 1986

■ Assumption

- Rectangular Parallelepiped (RPP) sensitive volume
- Constant LET all along ion path
- Q_{crit} critical charge of this sensitive volume
- If $Q_{dep} > Q_{crit}$ then an event occurs

■ CREME enables to calculate the SEU rate in a given sensitive volume characterized by a specific LET threshold

- Calculation parameters (a, b, c, Lth)

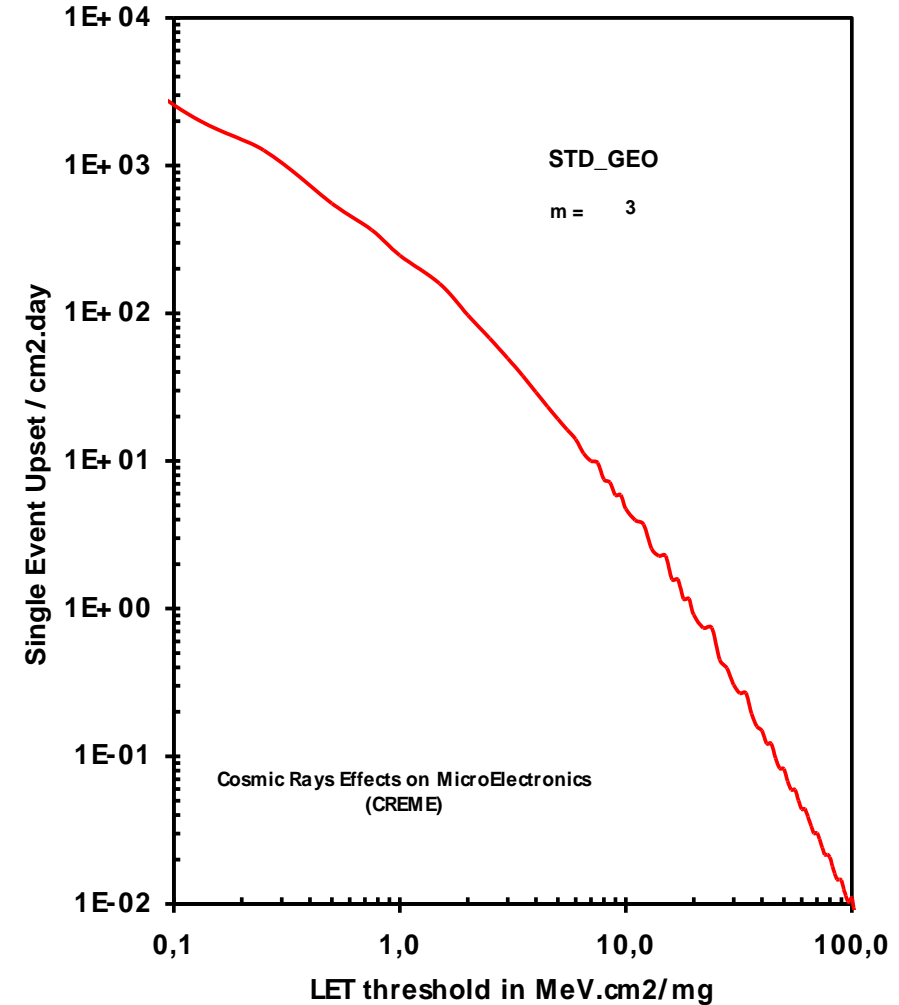


$$\Delta Q \geq Q_{crit} \longrightarrow \text{Event !}$$

$$\Delta Q \propto \Delta E = LET_{Si}^{ion}(E) \cdot \Delta x$$

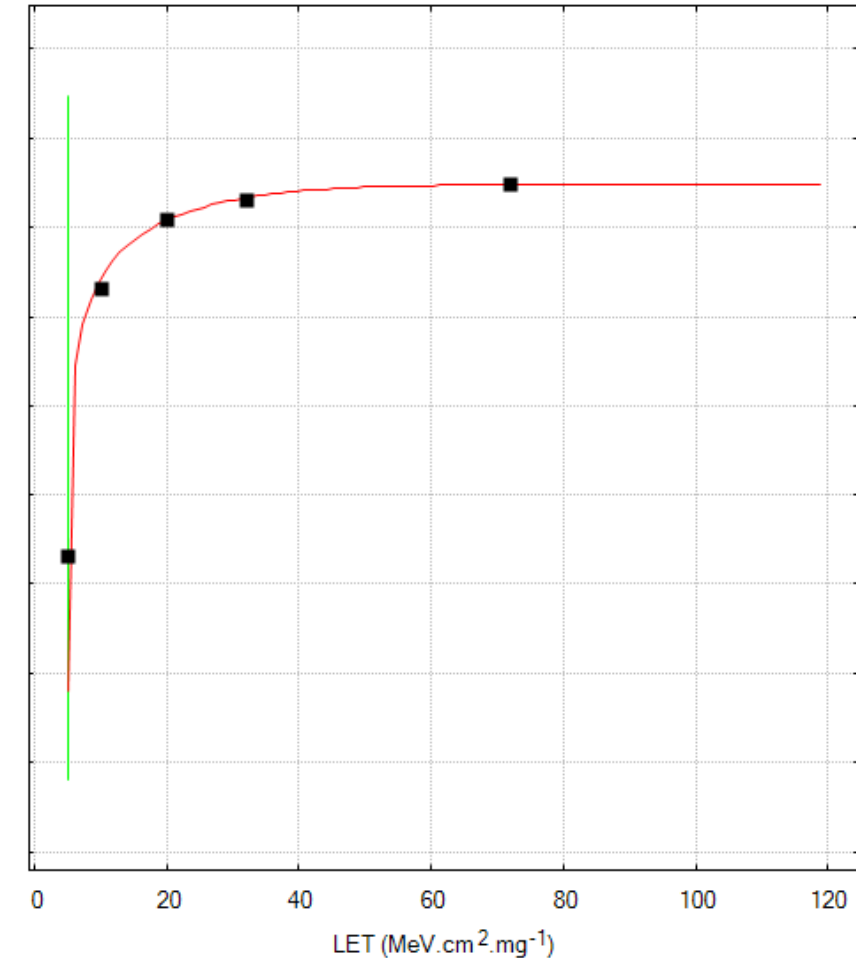
Single Cell Rate

- For a given sensitive volume
 - The SEU rate is calculated with the UPSET module of CREME86 (included in OMERE) for all possible LETth
- Single cell rate
- For the entire device
 - The single-cell rate is correlated to the device under-irradiation response with OMERE



Interpretation of Data

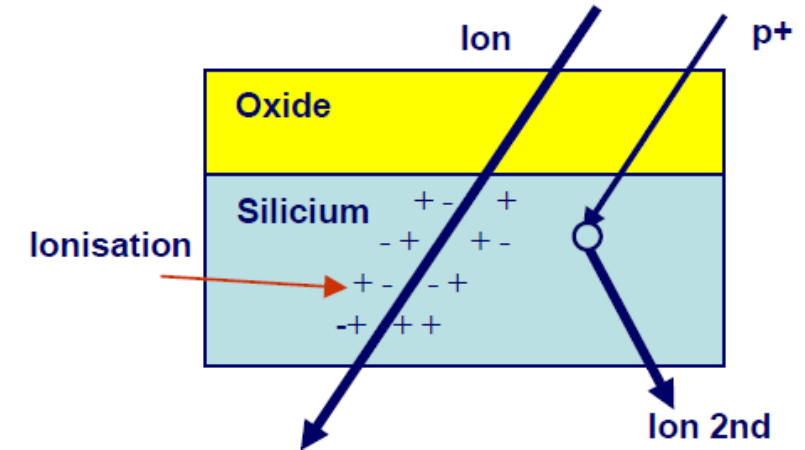
- All cells do not have the same LET threshold in a device
 - Progressive increase of the cross section curve
- The SEE susceptibility of the entire device (including all cells) versus LET is given by the cross section curve
 - The rate for one sensitive volume (one L_{th}) is calculated at each LET and integrated over the whole cross section curve
- This SEE rate is calculated by OMERE
 - With the CREME rate calculated for one cell with a specific LET threshold
 - Taking into account the whole device sensivity as a function of the LET



SEE Caused by Protons

■ Proton cross section

- ❑ Only one particle type (proton)
- ❑ No need to use the LET
- ❑ Proton-caused SEE are indirect
 - No geometry/angle effect taken into account
- ❑ Cross section expressed as the function of the incident energy
- ❑ Can be simulated from Heavy-ion data
(PROFIT / SIMPA/ METIS models available)



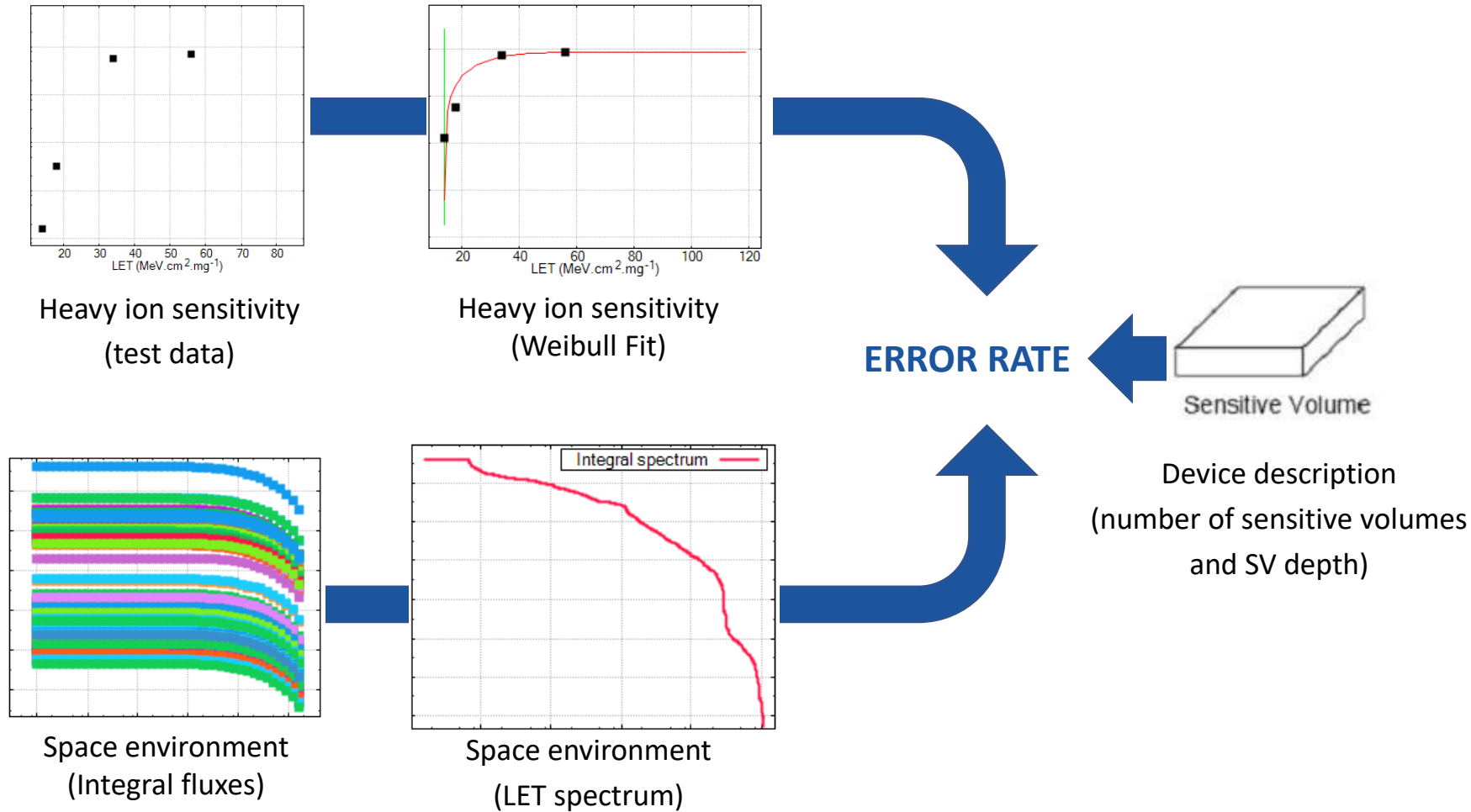
$$\tau_{p+} = \int_{E_0}^{\infty} \phi(E) \Sigma(E) dE$$

■ Proton SEE rate

- ❑ Product of the cross section multiplied by the flux at each energy

- Device considered as potentially sensitive to protons if the heavy ion LET threshold is smaller than $15 \text{ MeV.cm}^2.\text{mg}^{-1}$

SEE Rate: Heavy ion summary



Inputs needed:

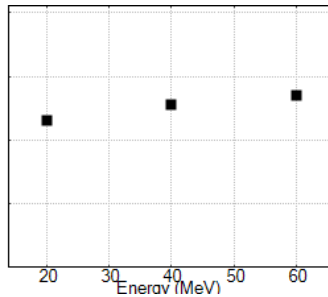
- Environment
- Heavy-Ion test data
- Number and depth of SV

Output:

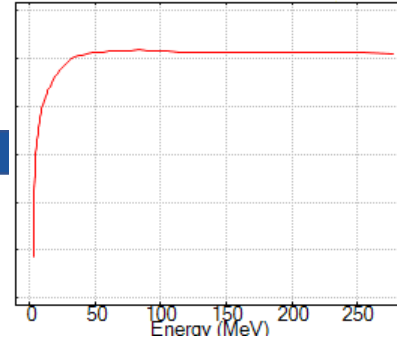
- SEE rate /day for each environment source



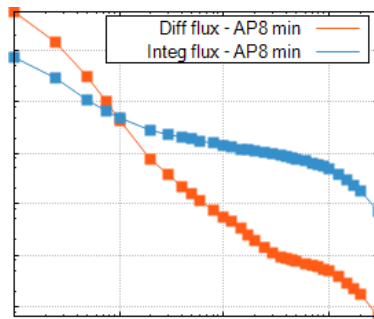
SEE Rate: Proton summary



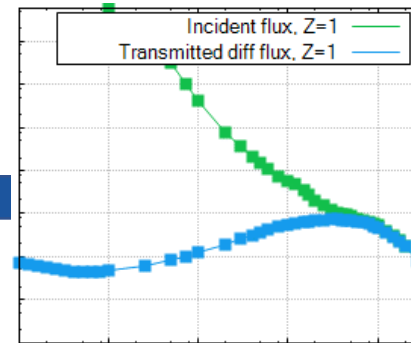
Proton sensitivity
OR
Heavy-ion sensitivity
(test data)



Proton sensitivity
(Weibull Fit)



Space environment
(Incident flux)



Space environment
(Transported flux)

ERROR RATE

Inputs needed:

- Environment
- Proton test data (or heavy-ion data + simulation model)

Output:

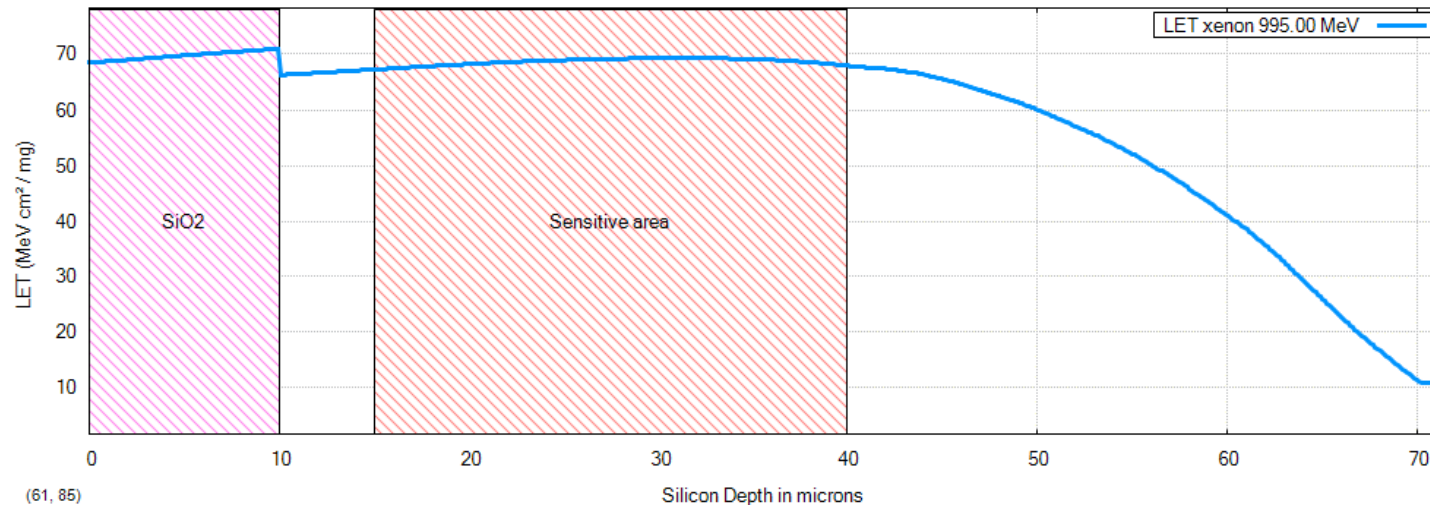
- SEE rate /day for each environment source

$$\tau_{p+} = \int_{E_0}^{\infty} \phi(E) \Sigma(E) dE$$



Effective LET

- In a heavy ion test, the LET given by the facility is the surface LET
- The LET does not keep a constant value in the device volume
- If the sensitive volume depth is known, the effective LET can be calculated
 - Averaged LET value in the die



Mean LET on the sensitive area ? X

Superstructure beyond Silicon

Number of layers : 1

Layer 1 : 10 Silicon dioxide (SiO₂) μm

Sensitive area in Silicon

X Min of sensitive area : 5 μm

X Max of sensitive area : 30 μm

The position of the sensitive area is calculated with respect to the Si surface

Particle and incident energy

Incident particle : Xe Energy : 995 MeV

Calculation

Results

Penetration depth in Si: 60.87 μm

Superstructure surface LET : 68.48 MeV cm² mg⁻¹

Sensitive area surface LET : 67.26 MeV cm² mg⁻¹

Mean LET in the sensitive area : 68.68 MeV cm² mg⁻¹

Length of the sensitive area : 25.00 μm

Deposited charge : 1.77e+01 pC

Output : C:\Users\Leo.coic\Documents\OMERE 5.6\LETe ...

Ok Cancel



Thank you for your attention

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Support available at omere@trad.fr

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